[redacted]

- V_{CE} =1350V
- I_C=40A@T_C=100
- $V_{CE(sat)}$=2.0V

- Trench and field-stop technologn[redacted]

BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	1350	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=1350V, V_{GE}=0V	-	-	100	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	100	nA
	Gate *e					

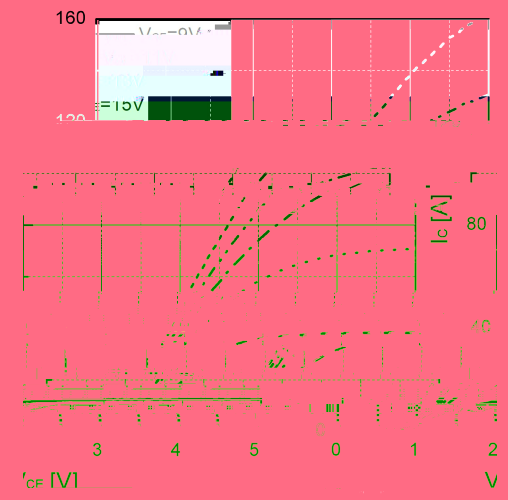

Fig 1. Typical output characteristic (T_{vj}=25)

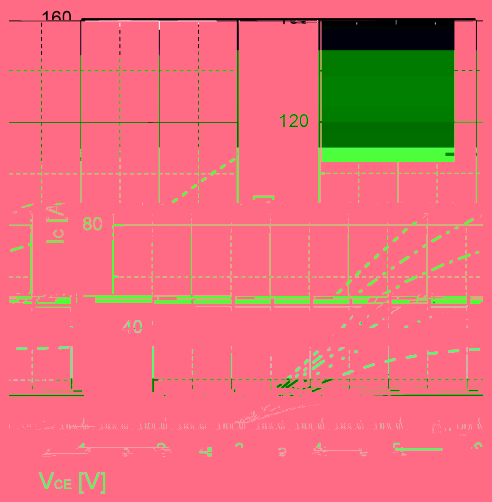

Fig 2. Typical output characteristic(T_{vj}=175)

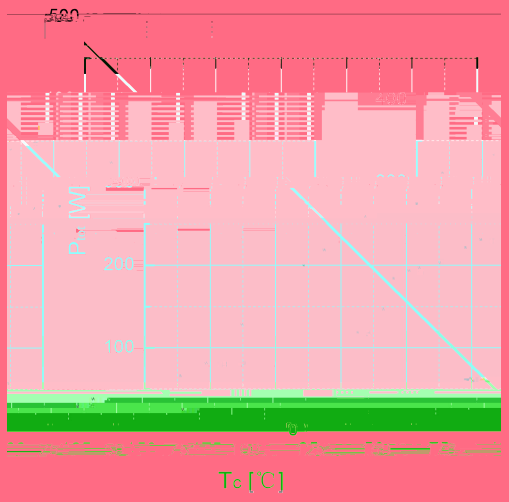

Fig 3. Power dissipation as a function of T_C

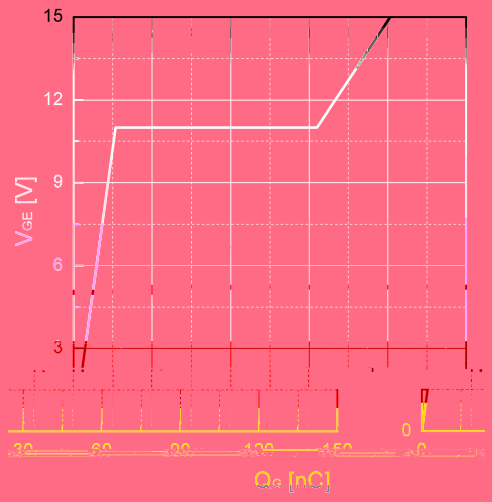

Fig 4. Typical Gate charge

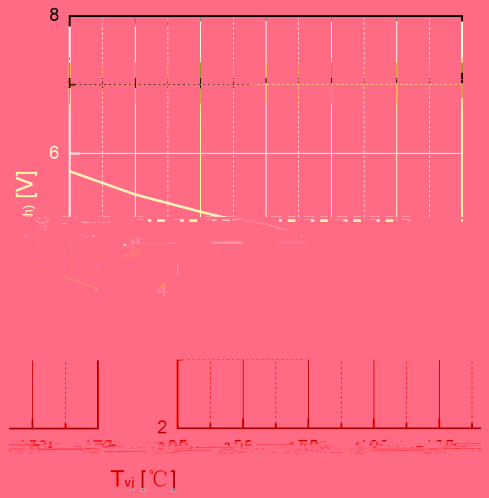

Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj} (I_C=1mA)

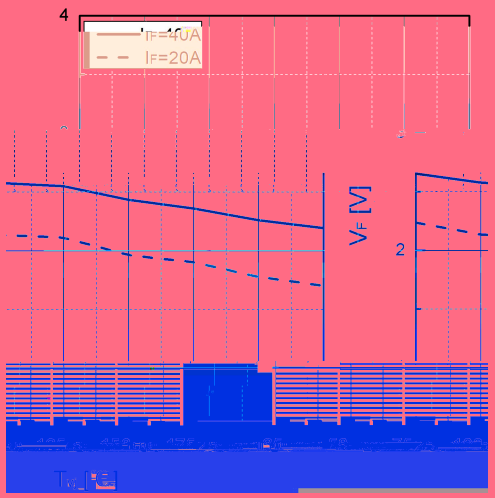

Fig 6. Typical V_F as a function of T_{vj}

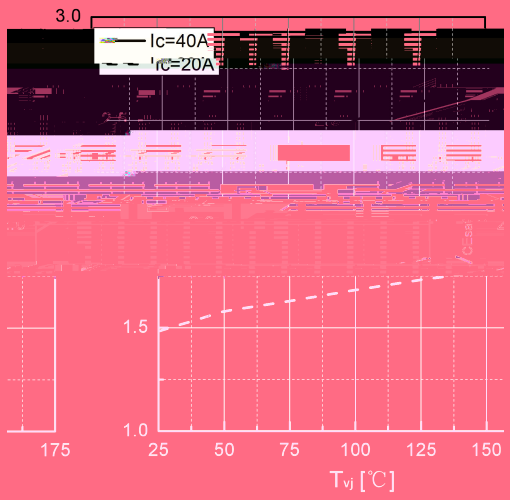

Fig 7. Typical V_{CEsat} as a function of T_{vj}

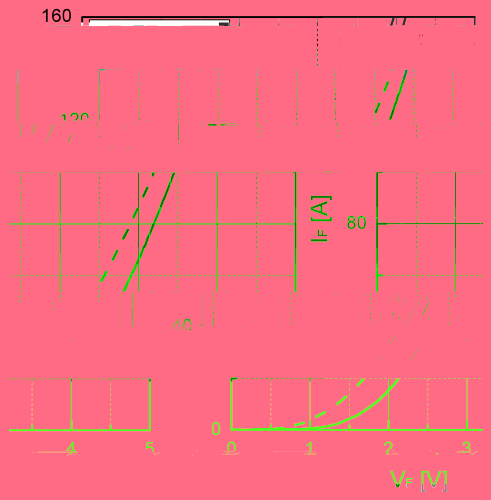

Fig 8. Typical I_F as a function of V_F

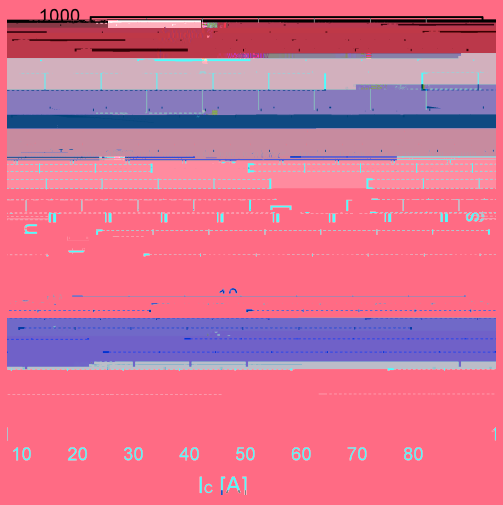

Fig 9. Typical switching time as a function of I_C

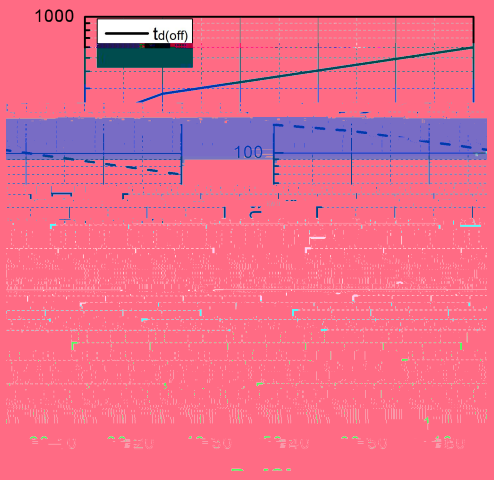

Fig 10. Typical switching times as a function of R_G

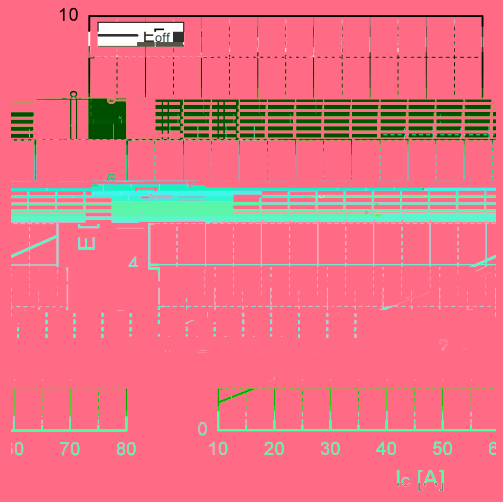

Fig 11. Typical switching energy losses as a function of I_C

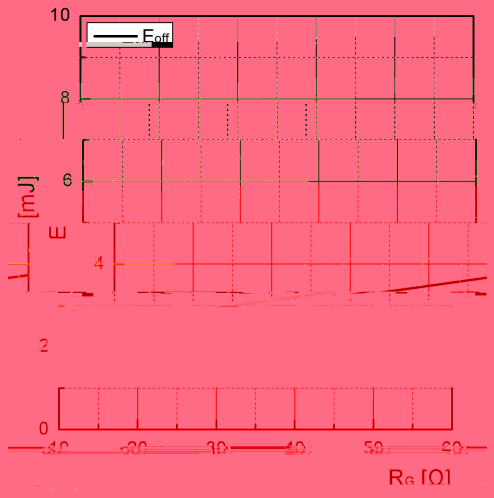

Fig 12. Typical switching energy losses as a function of R_G

Fig 13. Typical capacitance as a function of V_{CE} (f=1Mhz, V_{GE}=0V)

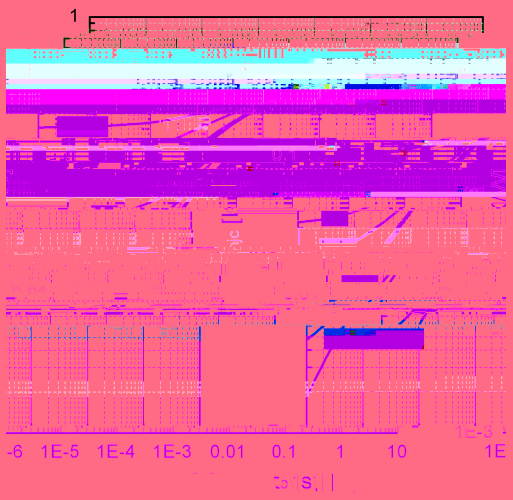

Fig 14. Transient thermal impedance of IGBT

Date	Revision	Changes
2025-02-05	Rev 1.0	Release of the preliminary datasheet.
2025-02-27	Rev 1.1	Add graph and character update